

PMBFJ108; PMBFJ109; PMBFJ110 N-channel junction FETs

Rev. 4 — 20 September 2011

Product data sheet

Product profile 1.

1.1 General description

Symmetrical N-channel junction FETs in a SOT23 package.

1.2 Features and benefits

- High-speed switching
- Interchangeability of drain and source connections
- Low R_{DSon} at zero gate voltage (< 8 Ω for PMBFJ108).

1.3 Applications

- Analog switches
- Choppers and commutators
- Audio amplifiers.

Pinning information 2.

Table 1.	Pinning		
Pin	Description ^[1]	Simplified outline	Symbol
1	drain	□3	
2	source		
3	gate		3 → 1 2 sym053

[1] Drain and source are interchangeable.



N-channel junction FETs

Ordering information 3.

Table 2. Ordering information					
Type number	Package				
	Name	Description	Version		
PMBFJ108	-	plastic surface mounted package; 3 leads	SOT23		
PMBFJ109					
PMBFJ110					

Marking 4.

Table 3. Marking	
Type number	Marking code ^[1]
PMBFJ108	38*
PMBFJ109	39*
PMBFJ110	40*

[1] * = p: Made in Hong Kong

* = t: Made in Malaysia

* = W: Made in China

Limiting values 5.

Table 4. **Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage (DC)		-	±25	V
V _{GSO}	gate-source voltage		-	-25	V
V_{GDO}	gate-drain voltage		-	-25	V
l _G	forward gate current (DC)		-	50	mA
P _{tot}	total power dissipation	$T_{amb} = 25 \ ^{\circ}C$	<u>[1]</u> -	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C

[1] Mounted on an FR4 printed-circuit board.

Thermal characteristics 6.

Table 5.	Thermal characteristics			
Symbol	Parameter	Conditions	Тур	Unit
R _{th(j-a)}	thermal resistance from junction to ambient		<u>[1]</u> 500	K/W

[1] Mounted on an FR4 printed-circuit board.

PMBFJ108_109_110

N-channel junction FETs

7. Static characteristics

Static characteristics					
Parameter	Conditions	Min	Тур	Max	Unit
gate-source leakage current	$V_{GS} = -15 \text{ V}; V_{DS} = 0 \text{ V}$	-	-	-3	nA
drain-source cut-off current	$V_{GS} = -10 \text{ V}; V_{DS} = 5 \text{ V}$	-	-	3	nA
drain-source leakage current					
PMBFJ108	$V_{GS} = 0 V; V_{DS} = 15 V$	80	-	-	mA
PMBFJ109	$V_{GS} = 0 V; V_{DS} = 15 V$	40	-	-	mA
PMBFJ110	$V_{GS} = 0 V; V_{DS} = 15 V$	10	-	-	mA
gate-source breakdown voltage	$I_G = -1 \ \mu A; \ V_{DS} = 0 \ V$	-	-	-25	V
gate-source cut-off voltage					
PMBFJ108	$I_{D} = 1 \ \mu A; \ V_{DS} = 5 \ V$	-10	-	-3	V
PMBFJ109	$I_{D} = 1 \ \mu A; \ V_{DS} = 5 \ V$	-6	-	-2	V
PMBFJ110	$I_{D} = 1 \ \mu A; \ V_{DS} = 5 \ V$	-4	-	-0.5	V
drain-source on-state resistance					
PMBFJ108	$V_{GS} = 0 V; V_{DS} = 0.1 V$	-	-	8	Ω
PMBFJ109	$V_{GS} = 0 V; V_{DS} = 0.1 V$	-	-	12	Ω
PMBFJ110	$V_{GS} = 0 V; V_{DS} = 0.1 V$	-	-	18	Ω
	Parametergate-source leakage currentdrain-source cut-off currentdrain-source leakage currentPMBFJ108PMBFJ109PMBFJ110gate-source breakdown voltagegate-source cut-off voltagePMBFJ108PMBFJ109PMBFJ109PMBFJ109PMBFJ109PMBFJ109PMBFJ110drain-source on-state resistancePMBFJ108PMBFJ109PMBFJ109	Parameter Conditions gate-source leakage current $V_{GS} = -15 \text{ V}; V_{DS} = 0 \text{ V}$ drain-source cut-off current $V_{GS} = -10 \text{ V}; V_{DS} = 5 \text{ V}$ drain-source leakage current PMBFJ108 $V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$ PMBFJ109 $V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$ PMBFJ110 PMBFJ110 $V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$ gate-source breakdown voltage IG = -1 $\mu A; V_{DS} = 0 \text{ V}$ IG = -1 $\mu A; V_{DS} = 5 \text{ V}$ PMBFJ108 ID = 1 $\mu A; V_{DS} = 5 \text{ V}$ PMBFJ109 ID = 1 $\mu A; V_{DS} = 5 \text{ V}$ PMBFJ109 ID = 1 $\mu A; V_{DS} = 5 \text{ V}$ PMBFJ109 ID = 1 $\mu A; V_{DS} = 5 \text{ V}$ PMBFJ109 ID = 1 $\mu A; V_{DS} = 5 \text{ V}$ PMBFJ109 VGS = 0 \text{ V}; V_{DS} = 0.1 \text{ V} PMBFJ108 $V_{GS} = 0 \text{ V}; V_{DS} = 0.1 \text{ V}$	Parameter Conditions Min gate-source leakage current $V_{GS} = -15 V$; $V_{DS} = 0 V$ - drain-source cut-off current $V_{GS} = -10 V$; $V_{DS} = 5 V$ - drain-source leakage current VGS = 0 V; $V_{DS} = 15 V$ 80 PMBFJ108 $V_{GS} = 0 V$; $V_{DS} = 15 V$ 40 PMBFJ109 $V_{GS} = 0 V$; $V_{DS} = 15 V$ 40 PMBFJ110 $V_{GS} = 0 V$; $V_{DS} = 15 V$ 10 gate-source breakdown voltage $I_G = -1 \mu A$; $V_{DS} = 0 V$ - gate-source cut-off voltage - - PMBFJ108 $I_D = 1 \mu A$; $V_{DS} = 5 V$ -10 PMBFJ109 $I_D = 1 \mu A$; $V_{DS} = 5 V$ -6 PMBFJ110 $I_D = 1 \mu A$; $V_{DS} = 5 V$ -4 drain-source on-state resistance - - PMBFJ108 $V_{GS} = 0 V$; $V_{DS} = 0.1 V$ - PMBFJ109 $V_{GS} = 0 V$; $V_{DS} = 0.1 V$ -	ParameterConditionsMinTypgate-source leakage current $V_{GS} = -15 V; V_{DS} = 0 V$ drain-source cut-off current $V_{GS} = -10 V; V_{DS} = 5 V$ drain-source leakage currentPMBFJ108 $V_{GS} = 0 V; V_{DS} = 15 V$ 80-PMBFJ109 $V_{GS} = 0 V; V_{DS} = 15 V$ 40-PMBFJ110 $V_{GS} = 0 V; V_{DS} = 15 V$ 10-gate-source breakdown voltage $I_G = -1 \mu A; V_{DS} = 0 V$ gate-source cut-off voltagePMBFJ108 $I_D = 1 \mu A; V_{DS} = 5 V$ -10-PMBFJ109 $I_D = 1 \mu A; V_{DS} = 5 V$ -4-drain-source on-state resistance-4-PMBFJ108 $V_{GS} = 0 V; V_{DS} = 0.1 V$ PMBFJ109 $V_{GS} = 0 V; V_{DS} = 0.1 V$	ParameterConditionsMinTypMaxgate-source leakage current $V_{GS} = -15 V; V_{DS} = 0 V$ 3drain-source cut-off current $V_{GS} = -10 V; V_{DS} = 5 V$ 3drain-source leakage currentVGS = 0 V; V_{DS} = 15 V80PMBFJ108 $V_{GS} = 0 V; V_{DS} = 15 V$ 80PMBFJ109 $V_{GS} = 0 V; V_{DS} = 15 V$ 40PMBFJ109 $V_{GS} = 0 V; V_{DS} = 15 V$ 10gate-source breakdown voltage $I_G = -1 \mu A; V_{DS} = 0 V$ 25gate-source cut-off voltage $I_D = 1 \mu A; V_{DS} = 5 V$ -103PMBFJ108 $I_D = 1 \mu A; V_{DS} = 5 V$ -6-2-2PMBFJ109 $I_D = 1 \mu A; V_{DS} = 5 V$ -4-0.5-0.5drain-source on-state resistancePMBFJ108 $V_{GS} = 0 V; V_{DS} = 0.1 V$ 8PMBFJ109 $V_{GS} = 0 V; V_{DS} = 0.1 V$ 12

8. Dynamic characteristics

Table 7.Dynamic characteristics $T_{v} = 25 \circ C$ unless otherwise specified

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
C _{iss}	input capacitance	$V_{DS} = 0 V; V_{GS} = -10 V; f = 1 MHz$		-	15	30	pF
		V_{DS} = 0 V; V_{GS} = 0 V; f = 1 MHz; T_{amb} = 25 °C		-	50	85	pF
C _{rss}	feedback capacitance	$V_{DS} = 0 V; V_{GS} = -10 V; f = 1 MHz$		-	8	15	pF
Switching	g times (see <mark>Figure 2</mark>)						
t _d	delay time		[1]	-	2	-	ns
t _{on}	turn-on time		<u>[1]</u>	-	4	-	ns
t _s	storage time		<u>[1]</u>	-	4	-	ns
t _{off}	turn-off time		[1]	-	6	-	ns

[1] Test conditions for switching times are as follows:

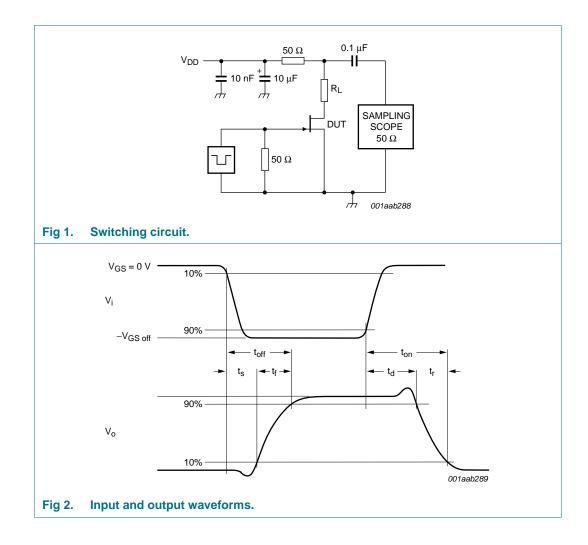
 V_{DD} = 1.5 V, V_{GS} = 0 V to V_{GSoff} (all types);

 V_{GSoff} = -12 V, R_L = 100 Ω (PMBFJ108);

 V_{GSoff} = -7 V, R_L = 100 Ω (PMBFJ109);

 V_{GSoff} = -5 V, R_L = 100 Ω (PMBFJ110).

N-channel junction FETs



PMBFJ108_109_110
Product data sheet

N-channel junction FETs

9. Package outline

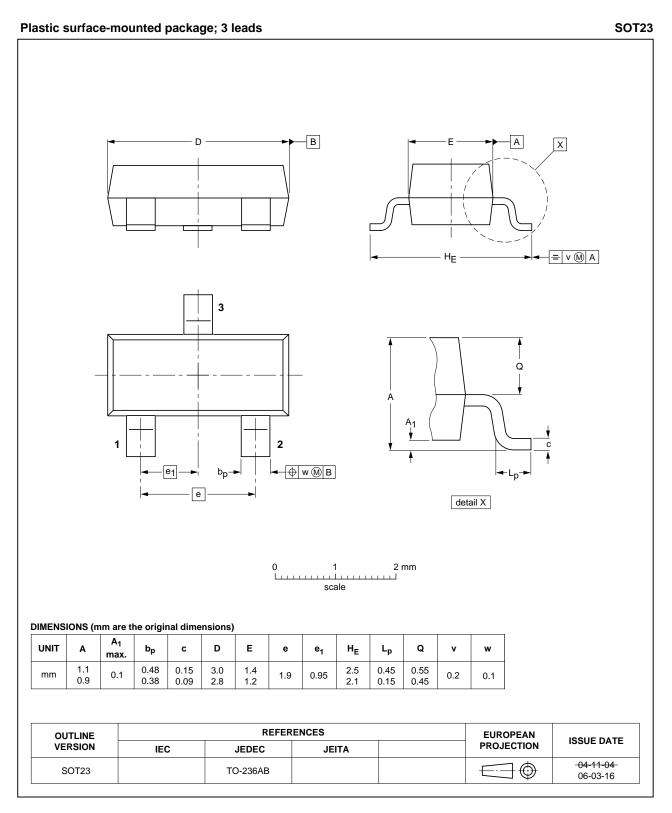


Fig 3. Package outline.

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PMBFJ108_109_110

N-channel junction FETs

10. Revision history

Table 8.Revision history				
Document ID	Release date	Data sheet status	Change notice	Supersedes
PMBFJ108_109_110 v.4	20110920	Product data sheet	-	PMBFJ108_109_110 v.3
Modifications:	guidelines o	of NXP Semiconductors.	-	comply with the new identity ame where appropriate.
	 Package ou 	tline drawings have bee	n updated to the la	atest version.
PMBFJ108_109_110 v.3 (9397 750 13401)	20040804	Product data sheet	-	PMBFJ108_109_110_CNV v.2
PMBFJ108_109_110_CNV v.2	19971201	Product specification	-	-

11. Legal information

11.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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7 of 9

N-channel junction FETs

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N-channel junction FETs

13. Contents

1	Product profile 1
1.1	General description 1
1.2	Features and benefits 1
1.3	Applications 1
2	Pinning information 1
3	Ordering information 2
4	Marking 2
5	Limiting values 2
6	Thermal characteristics 2
7	Static characteristics 3
8	Dynamic characteristics 3
9	Package outline 5
10	Revision history 6
11	Legal information7
11.1	Data sheet status 7
11.2	Definitions7
11.3	Disclaimers 7
11.4	Trademarks 8
12	Contact information 8
13	Contents 9

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